

What is claimed is:

1. A semiconductor device wherein:

a principal surface of a semiconductor base board is ground mirror-finished such that a breakable layer on the principal surface is removed and a crystalline layer which is disposed innermore than the breakable layer is exposed;

bumps are formed on a predetermined position on other principal surface of the semiconductor base board.

2. Method for manufacturing a semiconductor device having the steps for:

grinding a principal surface on a semiconductor base board;

mirror-finishing the principal surface so as to remove a breakable layer on the principal surface and expose a crystalline layer which is disposed innermore than the breakable layer; and

forming bumps on predetermined positions on other principal surface on the semiconductor base board.

3. Method according to Claim 2 for manufacturing a semiconductor device wherein a principal surface on a semiconductor base board is ground after the other principal surface on the semiconductor base board is coated by a protecting member.